

Philips Semiconductors

Data sheet	
status	Objective specification
date of issue	October 1991

UAA2090T

900 MHz front end circuit for cordless communication

FEATURES

- Operating frequency range up to 870 MHz
- Wide pre-amplifier AGC range
- IF frequency range from 0 up to 1 MHz
- Low noise figure
- Mode select input for one IF mixer/amplifier
- Supply voltage down to 3 V
- Low current consumption
- Stand-by mode
- Reference voltage output

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{P1}	supply voltage (pin 3)	3	5	5.5	V
V_{P2}	supply voltage (pin 17)	3	5	5.5	V
I_P	supply current (I_{3+17})	-	7.5	9	mA
	stand-by current	-	20	40	μ A
V_{ref}	reference output voltage (pin 13)	1.44	1.6	1.76	V
$f_{i\text{ RF}}$	radio input frequency	-	870	-	MHz
G_V	pre-amplifier gain range	-	28	-	dB
NF	noise figure pre-amplifier	-	3.0	-	dB
T_{amb}	operating ambient temperature	-10	-	70	$^{\circ}$ C

INTEGRATED CIRCUITS
IC03

GENERAL DESCRIPTION

The UAA2090T is provided for cordless telephone applications according to CT2 standard; and it can be used in low-power applications (handsets) due to its low supply voltage and low power consumption. Independent of the receiver architecture, the UAA2090T can perform a convenient mix-down from radio frequencies to baseband level by mode selection. Further control functions reduce the amount of components and thus the size of handsets. The isolation between mixer injection frequency and RF input signal has been optimized.

ORDERING INFORMATION

EXTENDED TYPE NUMBER	PACKAGE			
	PINS	PIN POSITION	MATERIAL	CODE
UAA2090T	20	mini-pack	plastic	SOT163A

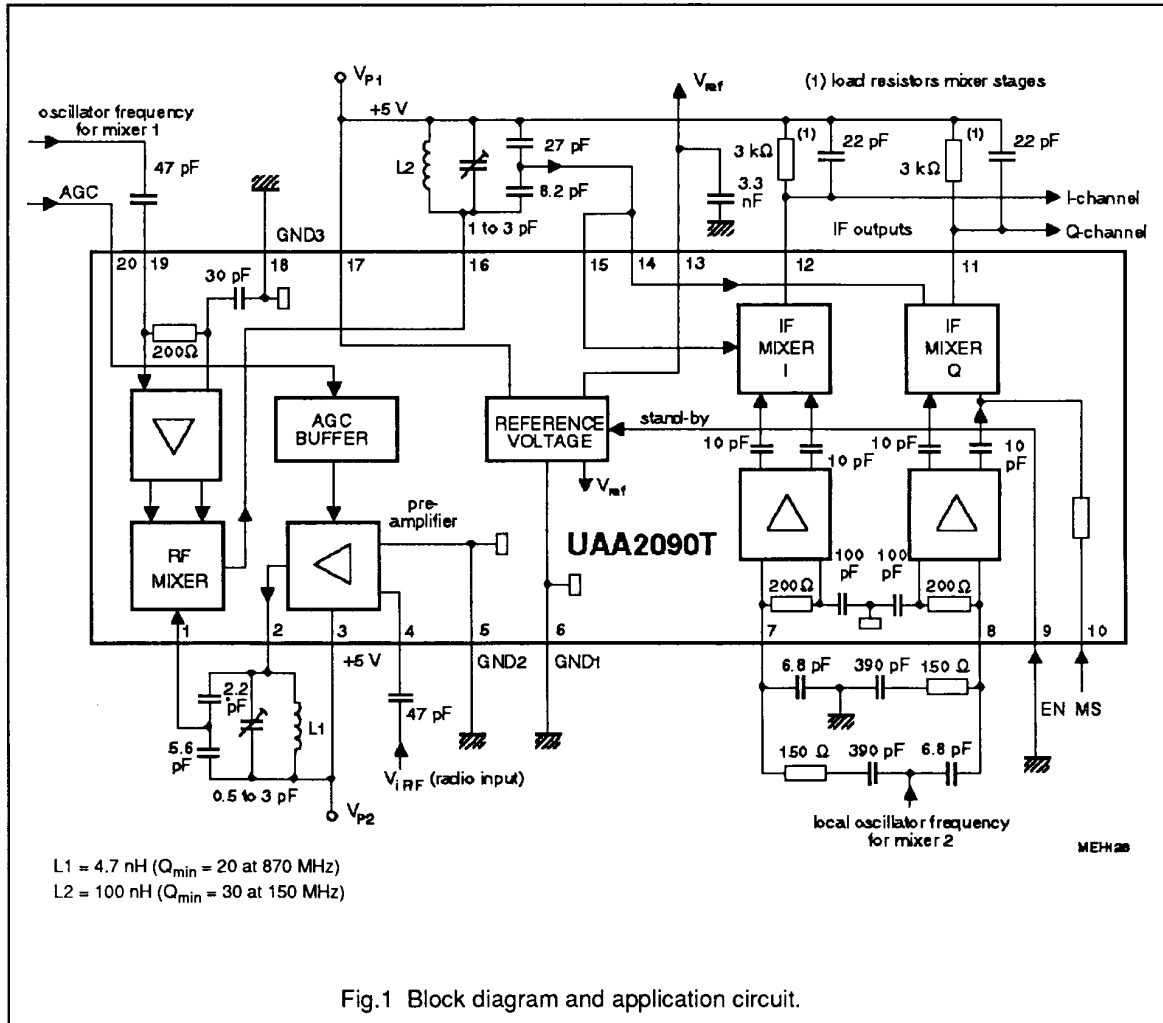
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PINNING

SYMBOL	PIN	DESCRIPTION
V_{iM1}	1	RF input signal to mixer 1
V_{oRF}	2	RF pre-amplifier output signal
V_{P2}	3	+5 V supply voltage for pre-amplifier
V_{iRF}	4	RF pre-amplifier input
GND2	5	ground 2 (0 V) for pre-amplifier
GND1	6	ground 1 (0 V)
V_{osMI}	7	local oscillator signal to mixer 2a (I-channel)
V_{osMQ}	8	local oscillator signal to mixer 2b (Q-channel)
EN	9	enable active LOW, switching from stand-by to run
MS	10	mode select
V_{oQ}	11	IF output signal of Q-channel
V_{oI}	12	IF output signal of I-channel
V_{ref}	13	1.6 V reference voltage output
V_{iMQ}	14	IF input signal of mixer 2b (Q-channel)
V_{iMI}	15	IF input signal of mixer 2a (I-channel)
V_{oM1}	16	mixer 1 output signal
V_{P1}	17	+5 V supply voltage
GND3	18	ground 3 (0 V) for mixer 1
V_{osM1}	19	oscillator signal for mixer 1
AGC	20	AGC input voltage for the pre-amplifier

PIN CONFIGURATION

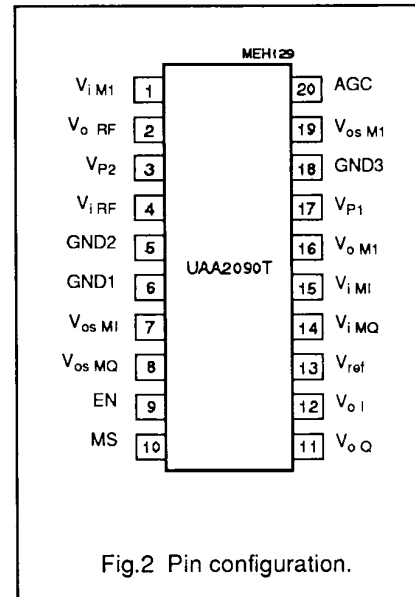


Fig.2 Pin configuration.

FUNCTIONAL DESCRIPTION

Pre-amplifier

The pre-amplifier has a diode-biased input with a typical bias current of 1 mA and input impedance of 50 Ω . The AGC voltage on pin 20 determines the pre-amplifier gain over a wide range. Since the output is open-collector, the maximum voltage gain is determined by the Q-factor of the external resonant circuit.

RF mixer

The RF mixer is an active, single-balanced mixer with typical bias current of 1 mA and with an open-collector output. The local oscillator input signal is fed to the

mixer via a buffer amplifier. The input impedance is 200 Ω .

IF mixers (I and Q)

Two separate IF mixers are provided to generate the I-channel IF and the Q-channel IF. The IF mixers are active, single-balanced mixers with typical bias currents of 1 mA and with open-collector outputs. The local oscillator input signals are fed to the mixers via buffer amplifiers with input impedances of 200 Ω (at 150 MHz).

Mode select (MS)

One of the IF mixers can be used as a simple linear amplifier for different applications in telephone sets (MS

connected to GND via a 20 k Ω resistor). The mixer can be switched off for other applications to reduce the supply current (MS connected to V_{P1}). MS is open-circuit for applications with two separate IF mixers.

Stand-by (EN)

When the voltage on pin 9 is $EN > V_{P1}/2 + 0.5$ V the band gap reference voltage is powered down. As a result, all bias currents are removed and the circuit is in the stand-by mode (supply current $I_p < 40$ μ A).

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_{P1}	supply voltage (pin 17)	-0.3	8.0	V
V_{P2}	supply voltage (pin 3)	-0.3	8.0	V
P_{tot}	total power dissipation	0	500	mW
T_{stg}	storage temperature range	-55	125	°C
T_{amb}	operating ambient temperature range	-10	70	°C
V_{ESD}	electrostatic handling* only for pins 6, 9, 13, 17 and 20	-	±2000	V

CHARACTERISTICS

$V_{P1} = V_{P2} = 5\text{ V}$ and $T_{amb} = -10\text{ to }70\text{ °C}$ (typical values measured at $T_{amb} = 25\text{ °C}$); measurements taken in Fig.3 (with resonance circuits L1, L2 and L3 short-circuited for DC measurements); input frequencies $f_{i\text{ RF}} = 866\text{ MHz}$ unmodulated and $f_{i\text{ IF}} = 150\text{ MHz}$ unmodulated unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{P1}	supply voltage range (pin 17)		3	5	5.5	V
V_{P2}	supply voltage range (pin 3)		3	5	5.5	V
I_P	supply current ($I_3 + I_{17}$)	$V_9 < 2\text{ V}$	-	7.5	9	mA
	supply current without mixers 2a and 2b	$V_{10} = V_{P1}; V_9 < 2\text{ V}$	-	3.5	-	mA
$I_{P\text{ off}}$	stand-by current	$V_9 > 3\text{ V}$	-	-	40	µA
Stand-by (pin 9)						
V_9	input voltage for stand-by		$V_P/2+0.5$	-	V_{P1}	V
	input voltage for run		0	-	$V_P/2-0.5$	V
t_{rec}	recovery time	from stand-by to run	-	-	1	ms
Reference voltage (pin 13)						
V_{ref}	reference output voltage	$I_{13} = -100\text{ µA}$	1.44	1.6	1.76	V
I_{13}	reference output current	note 1	-	-	-100	µA
Mode select switch MS (pin 10)						
V_{10}	input voltage for both IF mixers active	Fig.3	-	open-circuit		-
	input voltage for one IF mixer active	mixer Q operates as a linear amplifier	-	V_{ref}	-	V
	input voltage for IF mixers inactive	$I_P = 3.5\text{ mA}$	-	V_{P1}	-	V

* Equivalent to discharging a 100 pF capacitor through a 1.5 kΩ series resistor.

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
RF pre-amplifier		EMF1 = 866 MHz				
V_{iRF}	re-radiation of oscillator signals	measured on pin 4	-	-	-35	dBm
$Z_{4,5}$	input impedance		-	50	-	Ω
G_P	conversion power gain	$V_{20} = V_{ref} - 175$ mV	-	12	-	dB
ΔG_P	control range	$V_{20} = V_{ref} + 175$ mV	-28	-	-	dB
EMF1	3rd order intercept point		-13	-10	-	dBm
NF	noise figure	$T_{amb} = 25$ °C	-	3.0	6	dB
		$T_{amb} = -10$ to 70 °C	-	-	7	dB
AGC (pin 20)						
V_{20}	input voltage range	note 1		tbf		V
R_{20}	input resistance		-	100	-	k Ω
RF mixer (pins 1 and 19)						
R_1	input resistance	$f = 866$ MHz	-	870	-	Ω
C_1	input capacitance		-	1.2	-	pF
Z_{19}	input impedance	for EMF3 signal	-	200	-	Ω
G_P	conversion power gain		-	2	-	dB
EMF2	3rd order intercept point		-	-8	-11	dBm
NF	noise figure		-	15	17	dB
IF mixers I and Q (pins 7, 8, 14 and 15)		note 2				
$R_{14,15}$	input resistance	$f = 150$ MHz	-	tbf	-	Ω
$C_{14,15}$	input capacitance		-	tbf	-	pF
$Z_{7,8}$	input impedance	for EMF5 signal	-	200	-	Ω
G_P	conversion power gain		7	9	-	dB
EMF4	3rd order intercept point		0	2	-	dBm
NF	noise figure		-	13	16	dB
$\Delta\phi$	quadrature balance		-	-	± 4	deg
ΔA	amplitude balance		-	-	± 0.5	dB

Notes to the characteristics

1. The internal band gap reference voltage is internally decoupled. An AGC reference voltage of 1.6 V ($I_{13} < -100$ μ A) derived from the band gap reference must be externally decoupled.
2. All measurements and calculations are based on $R_S = 300$ Ω that is provided by the transformation network at the IF mixer input.

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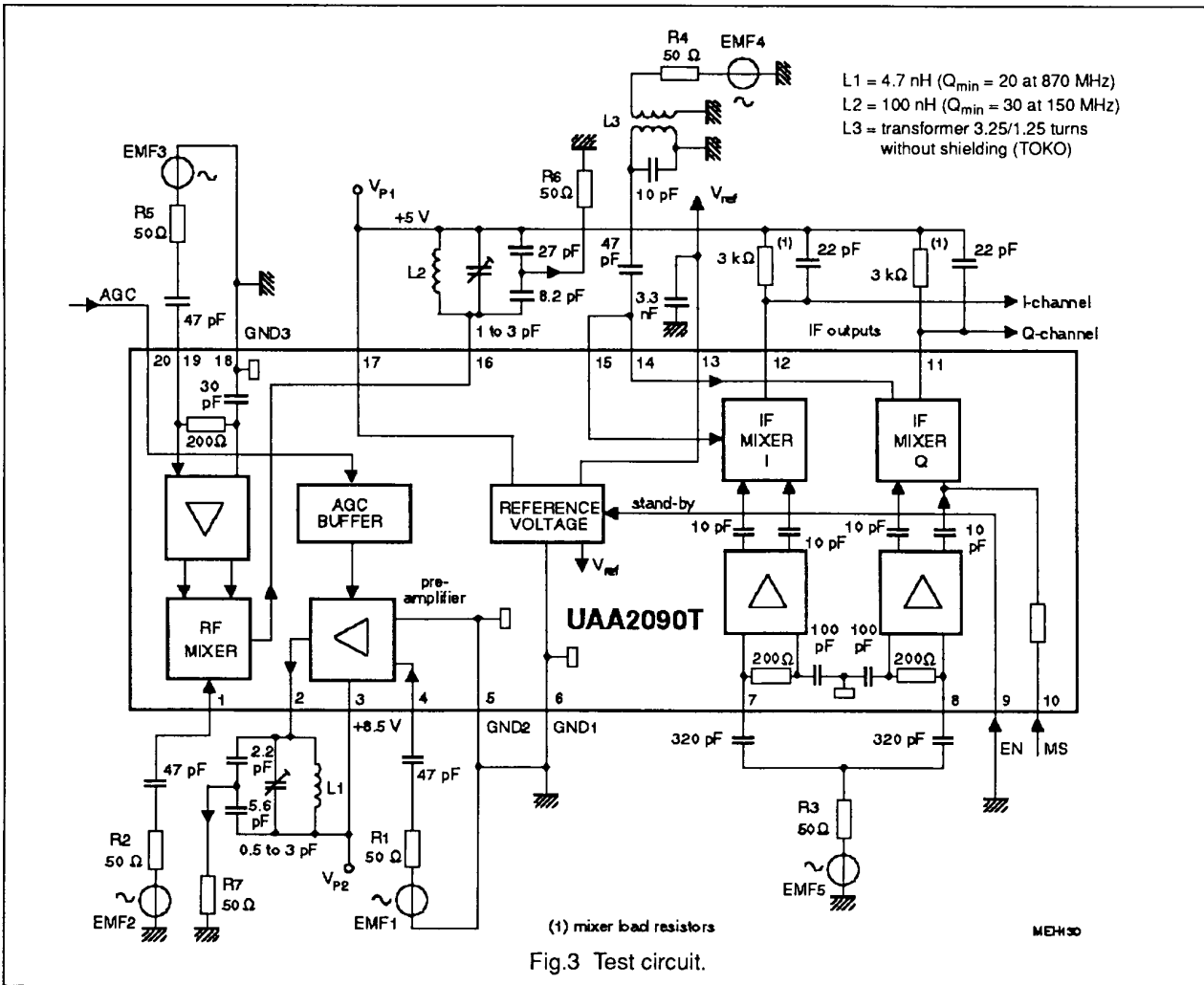


Fig.3 Test circuit.

AC TEST CONDITIONS

Noise figures, measured with gain and noise meter (Fig.4).

Pre-amplifier input signal (pin 4): EMF1; f = 866.000 MHz

RF mixer input signal (pin 1): EMF2; f = 866.000 MHz

RF mixer local oscillator signal (pin 19): EMF3 = -20 dBm; f = 716.000 MHz

IF mixer input signal (pin 15 or 14): EMF4; f = 150.000 MHz

IF mixer local oscillator signal (pin 7 or 8): EMF5 = -20 dBm; f = 150.100 MHz

Available power gain G_p

$$G_p = 10 \log \left((4 V_L^2 / V_S^2) \cdot (R_S / R_L) \right)$$

Re-radiation, measurements are taken from the 50 Ω series resistors of the oscillator signal inputs

EMS3 = -20 dBm; EMS5 = -20 dBm

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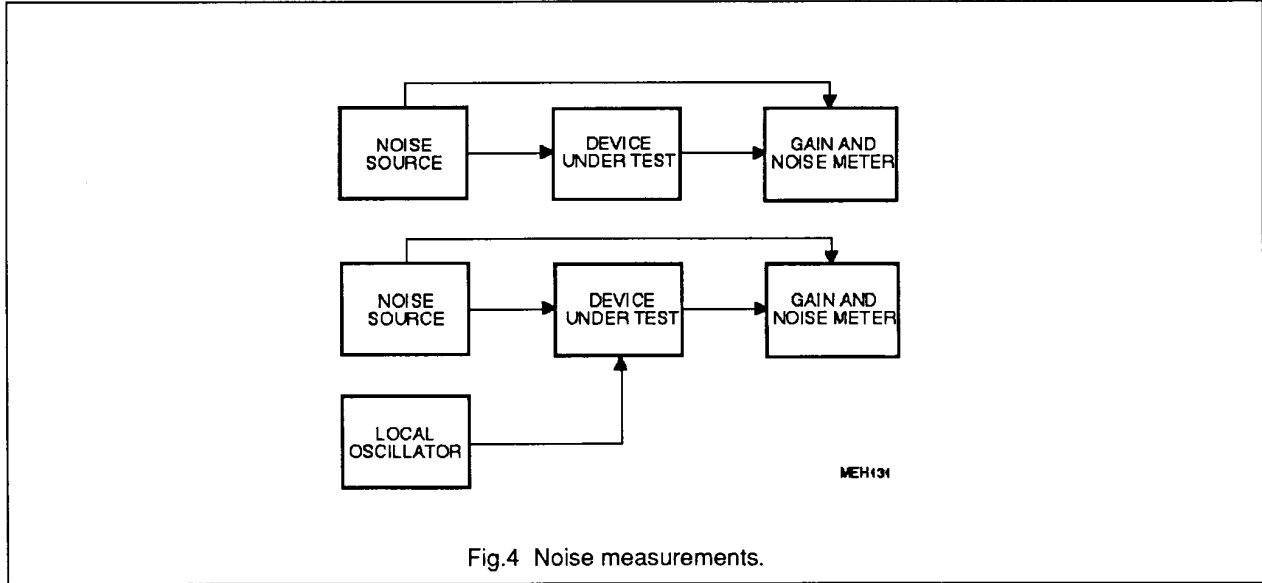


Fig.4 Noise measurements.

3rd order interception point IP3 (Fig.5)

Input signal (pin 4):
Input signal (pin 1):

EMF1 = -30 dBm; f2 = 866.010 MHz
EMF2 = -30 dBm; f1 = 866.000 MHz

$V_{IP3} = EMF2/dBm - IL_{PC}/dB + 0.5 IM3/dB$

IL_{PC} = insertion loss of power combiner

Baseband output, amplitude and phase balance for I-channel and Q-channel

Local oscillator input signal (pin 7 or 8): EMF3 = -20 dBm
Amplitude balance is derived from voltage gain measurements;
phase balance is measured with a differential phase meter.

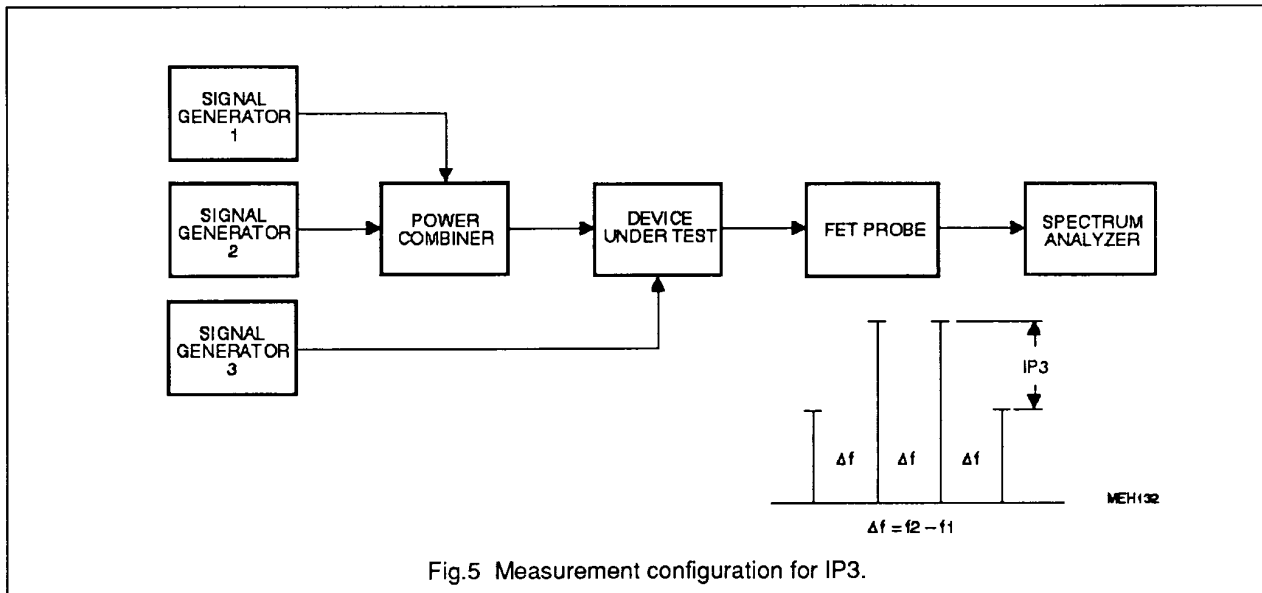


Fig.5 Measurement configuration for IP3.

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APPLICATION INFORMATION

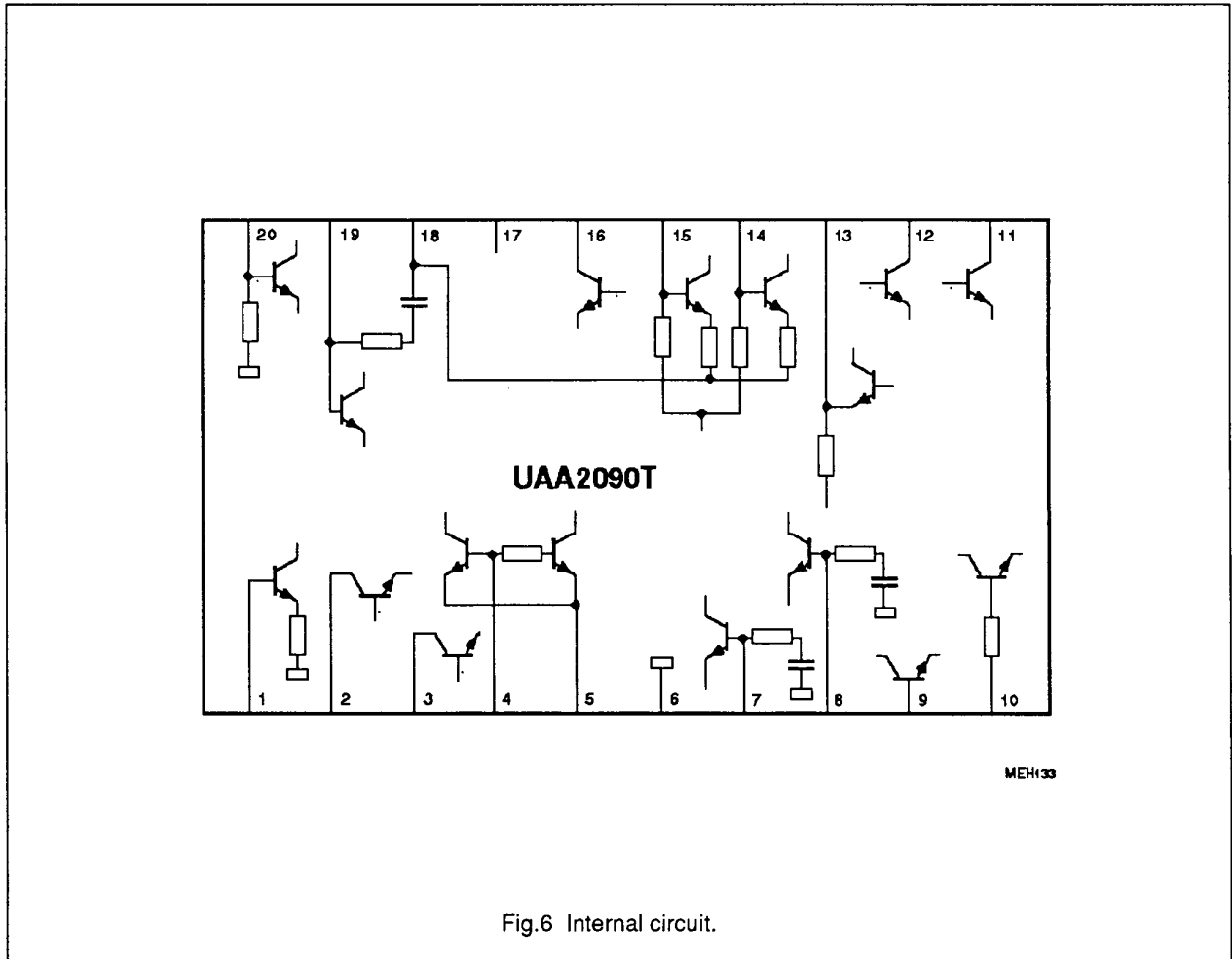


Fig.6 Internal circuit.

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PRINT LAYOUT

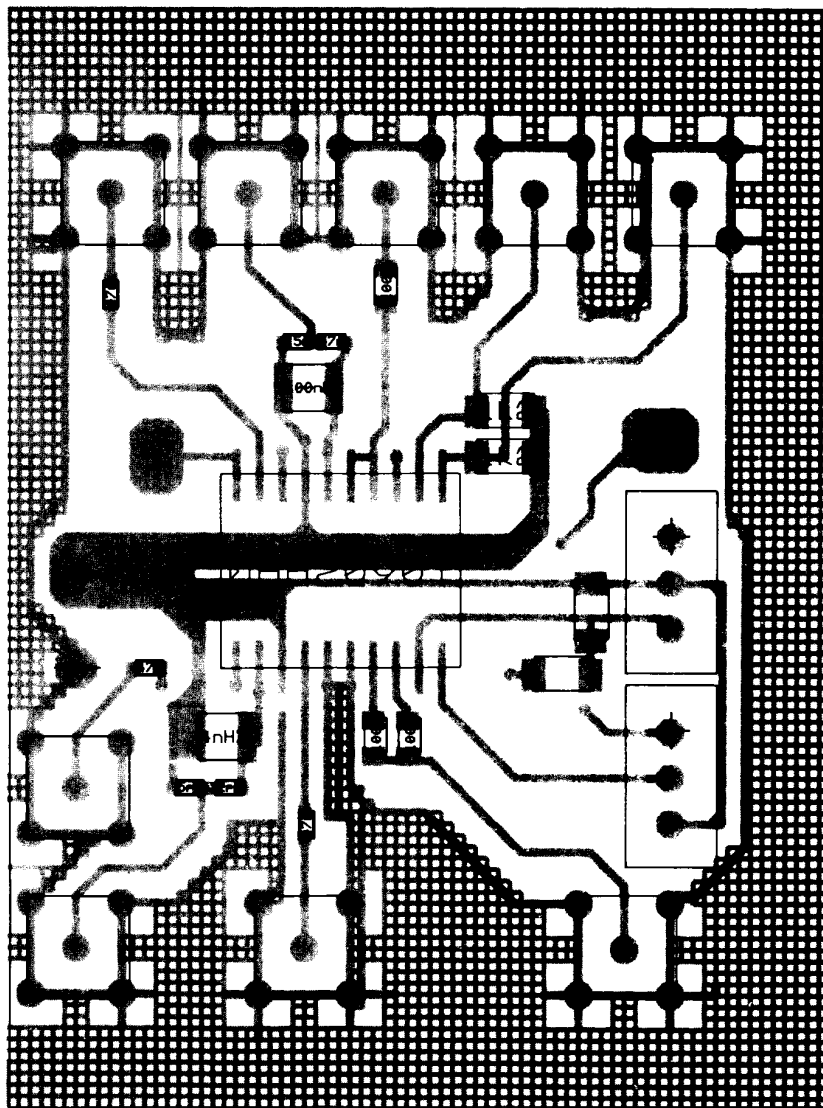


Fig.7 Print layout of side 1 (lower drawing with components).

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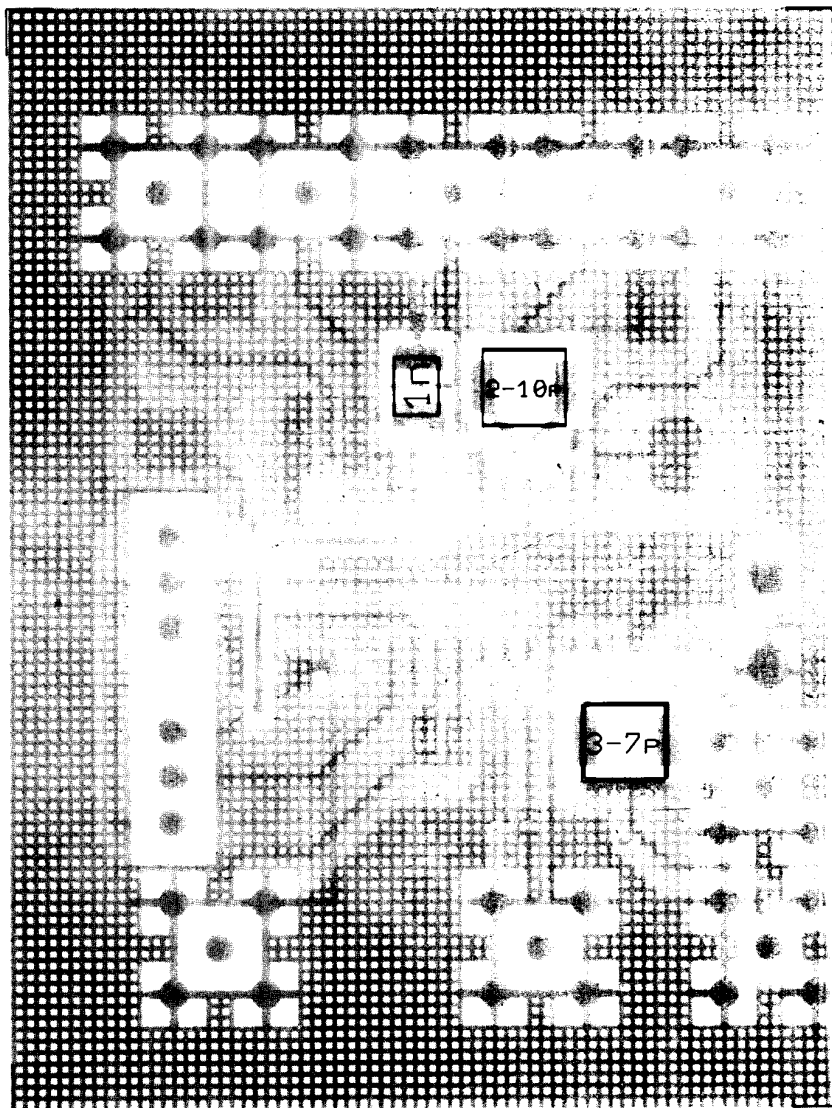
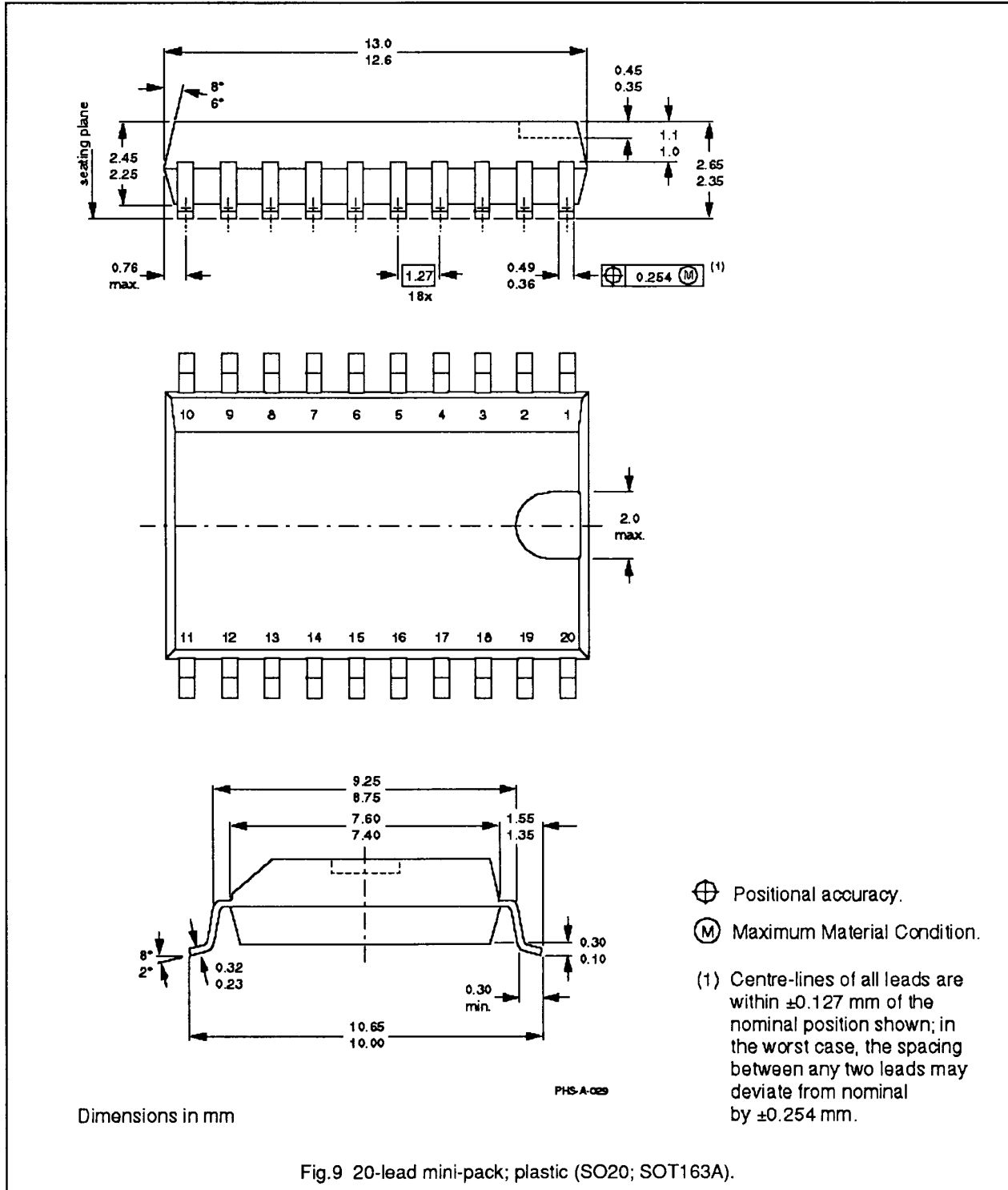


Fig.8 Print layout of side 2 (lower drawing with components).

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PACKAGE OUTLINE



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SOLDERING

Plastic mini-packs

BY WAVE

During placement and before soldering, the component must be fixed with a droplet of adhesive. After curing the adhesive, the component can be soldered. The adhesive can be applied by screen printing, pin transfer or syringe dispensing.

Maximum permissible solder temperature is 260 °C, and maximum duration of package immersion in solder bath is 10 seconds, if allowed to cool to less than 150 °C within 6 seconds. Typical dwell time is 4 seconds at 250 °C.

A modified wave soldering technique is recommended using two solder waves (dual-wave), in which a turbulent wave with high upward pressure is followed by a smooth, laminar wave. Using a mildly-activated flux eliminates the need for removal of corrosive residues in most applications.

BY SOLDER PASTE REFLOW

Reflow soldering requires the solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the substrate by screen printing, stencilling or pressure-syringe dispensing before device placement.

Several techniques exist for reflowing, for example, thermal conduction by heated belt, infrared, and vapour-phase reflow. Dwell times vary between 50 and 300 seconds according to the method. Typical reflow temperatures range from 215 to 250 °C.

Pre-heating is necessary to dry the paste, to evaporate the binding agent.

Pre-heating duration: 45 minutes at 45 °C.

REPAIRING SOLDERED JOINTS (BY HAND-HELD SOLDERING IRON OR PULSE-HEATED SOLDER TOOL)

Fix the component by first soldering two, diagonally opposite end pins. Apply the heating tool to the flat part of the pin only. Contact time must be limited to 10 seconds up to 300 °C. When using proper tools, all other pins can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C. (Pulse-heated soldering is not recommended for SO packages).

For pulse-heated solder tool (resistance) soldering of VSO packages, solder is applied to the substrate by dipping or by an extra thick tin/lead plating before package placement.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
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